

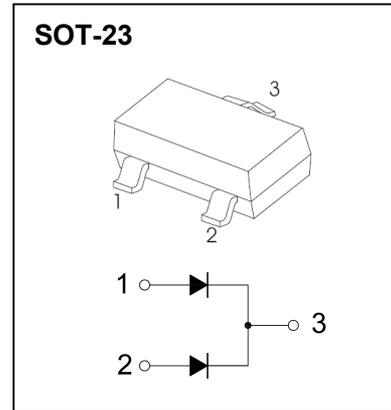
Plastic-Encapsulate Diodes

LOW LEAKAGE DIODE

FEATURES

- Low Leakage
- High Conductance

MARKING: A14



MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_R	DC Blocking Voltage	200	V
I_O	Continuous Forward Current	200	mA
I_{FM}	Peak Forward Current	700	mA
I_{FSM}	Non-repetitive Peak Forward Surge Current @t=1s	1	A
	@t=1ms	2	A
P_D	Power Dissipation	350	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	357	$^{\circ}\text{C}/\text{W}$
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	$I_R=5\mu\text{A}$	200			V
Reverse current	I_R	$V_R=180\text{V}$			10	nA
Forward voltage	V_F	$I_F=1\text{mA}$			0.75	V
		$I_F=10\text{mA}$			0.85	
		$I_F=50\text{mA}$			0.95	
		$I_F=100\text{mA}$			1.1	
		$I_F=200\text{mA}$			1.3	
		$I_F=300\text{mA}$			1.5	
Total capacitance	C_{tot}	$V_R=0\text{V}, f=1\text{MHz}$			4	pF